Iron self-di usion in $FeZr/^{57}FeZrmultilayersmeasured$ by neutron rejectometry: E ect of applied compressive stress

Mukul Gupta 1;2 and Ajay Gupta , Sujoy Chakravarty , Rachana Gupta 1;2 and Thomas Gutberlet UGC-DAE Consortium for Scientic Research, Khandwa Road, Indore, 452017, India Laboratory for Neutron Scattering, ETH Zurich and Paul Scherrer Institute, CH-5232 Villigen PSI, Switzerland (Dated: December 26, 2021)

Iron self-di usion in nano-composite FeZr alloy has been investigated using neutron rejectometry technique as a function of applied compressive stress. A composite target of Fe+Zr and 57 Fe+Zr was alternatively sputtered to deposite them ically homogeneous multilayer (CHM) structure, $f^{\rm tatrural}$ Fe_{75} Zr_{25}/ 57 Fe_{75} Zr_{25} h_0 . The multilayers were deposited on to a bent Siwafer using a 3-point bending device. Post-deposition, the bending of the substrate was released which results in an applied compressive stress on to the multilayer. In the as-deposited state, the alloy multilayer forms an amorphous phase, which crystallizes into a nano-composite phase when heated at 373 K. Bragg peaks due to isotopic contrast were observed from CHM, when measured by neutron rejectivity, while x-ray rejectivity showed a pattern corresponding to a single layer. Self-di usion of iron was measured with the decay of the intensities at the Bragg peaks in the neutron rejectivity pattern after them alannealing at different temperatures. It was found that the self-diff usion of iron slows down with an increase in the strength of applied compressive stress.

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I. INTRODUCTION

During recent decades am orphous and nanocrystalline metals and alloys have been investigated as an important class of materials with the possibility of tailoring their properties over a wide range by controlling particle size and morphology. 1,2,3,4 M ore recently nano-composite alloys, in which nanocrystals are surrounded by an intergranular am orphous matrix, have attracted a great attention due to their interesting structural⁵ and magnetic properties.^{6,7,8} One of the favorable way to obtain a nano-composite alloy, is partial crystallization of the am orphous alloy. 2,9,10 The alloy structure obtained above the prim ary crystallization temperature of the parent am orphous phase, but below the secondary crystallization temperature, has been termed as nano-com posite phase. 11 Above the secondary crystallization temperature, the nano-composite structure fully crystallizes to form an equilibrium state of the alloy. Structurally, the nanocrystals obtained after primary crystallization are surrounded by an amorphous inter-granular phase to form a nano-com posite phase. 1,12 N ano-com posite alloys produced with an am orphous precursor are the basis of interesting soft-magnetic alloys known as FINEM ET 13, NANO PERM 14, HIT PERM 15. Since the nano-composite phases produced in these alloys is inherently a m etastable phase, di usion of the constituents would play an important role in understanding and determ ining their properties for long-standing applications. Hence, atom ic di usion in such alloys is the key phenom enon for selecting their applications. 16

The situation becomes more complicated when the nano-composite alloys are produced in the form of a thin lm. Deposition of thin lms on to a substrate is known to produce lms with a large intrinsic strain or stresses which often results from dierences in thermal expansion

(therm al stress) or from the microstructure of the deposited lm (intrinsic stress). 17,18,19 The intrinsic stresses may originate due to several factors (i) at the strained regions within the lm seg. grain-boundaries, dislocations, voids, impurities, etc. (ii) at the lm/substrate interface due to lattice mismatch, dierent therm alexpansion, etc. (iii) at the lm/vacuum interfaces due to surface stress, adsorption, etc. or (iv) due to a dynamic processes e.g. re-crystallization, interdiusion, etc. 20 These stresses may signicantly a ect the physical properties of the thin lms, including atomic diusion.

It is known that when a material is deposited in the thin Im state, the dission mechanism can be completely diserent as compared to bulk state of that material, even when the material is in purely elemental form. Such a behavior has been mainly attributed to an increased defect concentration, metastability and unrelaxed state of the material. Therefore an extrapolation of bulk dissivity may results in erroneous values of diffusivity in the case of thin Ims. Since many devices which are used for application are fabricated in the form of nm range thin Ims, self-dission measurements can be extremely in portant for their applications.

In order to study the nature of stresses on self-di usion we have chosen a simple binary FeZr alloy for this purpose. It was found that (as will be shown later) after annealing at 373 K, the alloy forms a nano-composite phase which further crystallizes above 600 K. The self-di usion of iron was measured in the nano-composite state as a function of applied stress. The samples were deposited on to a substrate with a known bending. An external stress on to an $f^{1\,\text{atrural}}Fe_{75}Z\,r_{25}/^{57}Fe_{75}Z\,r_{25}\,l_{10}$ multilayer was applied by releasing the bending of the substrate which resulted in an applied compressive stress on to the sample. Iron self-di usion measurements were carried out using neutron re-ectivity technique. It may be

noted that the neutron re ectivity is an excellent technique for studying self-di usion in nm range structures. Due to the fact that neutron scattering length densities for isotopes of an element are dierent, neutron re ectivity with depth resolution in sub nm range provides a unique opportunity for measuring self-di usion. Conventional cross-sectioning and depth-pro-ling techniques, such as radiotracer, secondary ion mass spectroscopy (SIMS) are not suitable form easuring self-di usion in nm range structures as the depth resolution available with cross-sectioning and depth-pro-ling techniques is of the order of a few nm.

In an earlier w or k^{21} we have demonstrated that neutron rejectivity is a technique which could be used to probe di usion lengths of the order of 0.1 nm, and diusion at temperatures less than 400 K could be measured. In the present work, the eject of compressive stress on the self-diusion of iron in nano-composite multilayers was studied using neutron rejectivity.

II. SAMPLE PREPARATION AND CHARACTERIZATION

FeZr, CHM have been deposited on Si (100) substrates using magnetron sputtering technique. Smallpieces of Zr rods were pasted on the natural Fe and 57 Fe targets in a sym m etric way and the composite targets were sputtered alternately to prepare a chem ically homogeneous structure with nominal a composition $Si/[natrural Fe_{75}Zr_{25}]$ (25) nm $)/^{57}$ Fe₇₅ Z r₂₅ (10 nm) $]_{10}$. The deposition of the multilayerwas carried out after obtaining a base pressure better than 1 10 6 m bar. During the deposition, pressure in the chamber was 5 10^3 m bardue to 30 cm 3 /m in Ar gas ow used for sputtering of the targets. All the sam ples were deposited at a constant sputtering power of 50 W . Before deposition the vacuum chamber was repeatedly ushed with Argas so as to minimize the contamination of the remaining gases present in the chamber. Both the targets were pre-sputtered at least for 10 m in. During the deposition the substrate was mounted on a specially designed 3-point Siwafer bending device. The substrate was oscillated with respect to central position of the target for better uniform ity of the thickness of the deposited sample.

In all the cases, thin Siwafers (300 10) m were used as a substrate in order to avoid breaking during bending. The Siwafer was xed from both the ends, and by rotation of an asymmetric roller around the central axis, the bending height of the Siwafer can be varied between 0 to 5 mm. A pin-lock system was incorporated so that release of bending by itself could be avoided. A compressive stress is applied on to the deposited lm, when the bending of the Siwafer was released after deposition. The applied stress due to release of bending on to the Siwafer can be calculated using Stoney's formula²² and following a discussion given by Chen et al.²³ The applied

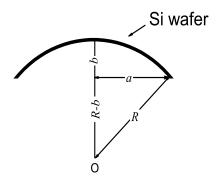


FIG. 1: Schematic diagram of the bent Siwafer, used for calculation of radius of curvature.

stress , is given by:

$$=\frac{\left(\frac{E_{Si}}{1}\right)T_{Si}^{2}}{6RT_{f}};$$
(1)

Where $(\frac{E_{S,i}}{1})$ is the biaxial modulus of the silicon substrate and is equal to 180.5 GPa. $E_{S,i}$ is Young's modulus for Si and $S_{S,i}$ is Poisson's ratio for Si. $T_{S,i}$ is the thickness of the substrate, T_{f} is the thickness of the lm and R is the radius of curvature. With the situation shown in the g.1, the radius of curvature can be written as:

$$R = \frac{a^2 + b^2}{2b};$$
 (2)

Combining equation (1) and (2), the value of stress was calculated. The param eter used in the present case are $T_{Si} = (300 \ 10) \ m$, $T_f = 370 \ nm$, $a = 40 \ mm$ and b was varied at 0, 3 and 5 mm. The obtained values of stress for the 3 cases are 0, 27 and 46 GPa. The errors in the calculation of applied stress were of the order of 15-20%, taking into account the uncertainties in the m easured physical param eters. Samples with dierent known bending were deposited under similar deposition conditions. A fter deposition and release of bending, the surface pro le of the sam ples was measured using a prolom eter. It was found that the surface of the samples was at and no changes in the surface pro le were observed for a sample prepared with or without bending. This indicated that even after the bending the substrate gains its original state and the stress is applied on to the deposited multilayer.

The composition of the deposited $\,$ lm swas determined using x-ray photoelectron spectroscopy (XPS) depth proling. The XPS pro $\,$ le was measured using monochromatic Al K x-rays ($\,$ lm m spot size) at the surface and at 3 dierent depths, after sputtering with Ar ions of 1 mA current and 3 kV accelerating voltage. The pressure during measurements was better than 1 $\,$ 10 $\,$ 8

m bar. The average composition of the lms was equal to Fe $_{75}$ 3 Zr $_{25}$ 3, excluding the data taken at the surface. Since at the surface, contributions from absorbed species like carbon and oxygen were signicant, the average composition of the lm was determined with the data taken at 3 dierent depths. A small amount of oxygen was detected throughout the depth of the lm.

Structural characterizations of the samples were carried out with x-ray re ectivity (XRR) and grazing incidence di raction using a standard x-ray di ractom eter (XRD) with Cu-K x-rays. The crystallization behavior of the multilayers was exam ined using dierential scanning calorim etry (DSC) with NETZSCH, DSC equipped with extremely high sensitivity -Sensor. The conversion electron M ossbauer spectroscopy m easurem ents (CEMS) were performed for determining the local environment of 57 Fe in the sam ples. The measurements were carried out using a 50 m C i ⁵⁷C o-radiactive source in a R h m atrix and a gas ow proportional counter (He+4% CH4) for detection of conversion electrons. The isom er shifts were calibrated relative to Fe. Hysteresis loops as a function of azim uthal angle were measured using magneto optical Kerre ect (MOKE).

Self-di usion m easurem entswere perform ed using neutron re ectom etry technique at AMOR re ectom eter at the Swiss spallation neutron source (SINQ), at Paul Scherrer Institute, Switzerland. The re ectivity pattern was measured using two dierent angular settings (0.5 and 1.0) in the time-of-ight mode.

III. RESULTS AND DISCUSSION

A. Structural Properties

The multilayers prepared in this work have a periodicity only for iron isotopes, it is expected that x-ray reectivity of the multilayers would show a pattern corresponding to a single layer. Fig. 2 shows x-ray re ectivity pattern of the multilayer structure prepared at 0,27 and 46 GPa. As can be seen from the pattern, at the designed period of the multilayer there was no contrast for x-rays, which con m s the chem ical homogeneity of the layers. The x-ray re ectivity pattern was tted assuming a single layer and an 'bxide' layer of about 6 nm thickness on the surface of the multilayer, using a computer program based on Parratt's form alism .25 Such an oxide layer on the surface of the sample may stem because of absorbed oxygen or other light elem ents, when the sam ples are exposed to the atmosphere after deposition. Presence of such a layer was also evident from XPS measurements.

On the other hand the neutron re ectivity pattern (g.3), showed well-pronounced B ragg peaks arising due to isotopic contrast between natural Fe and 57 Fe. As can be seen from the gure, the sample prepared without any stress showed rather asymmetric B ragg peaks, while for the samples prepared with an applied stress, the peaks were more symmetric. Such an asymmetry of the B ragg

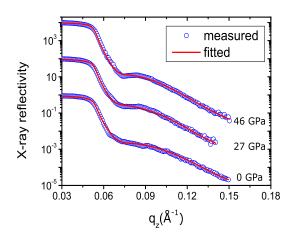


FIG. 2: (color online) X-ray re ectivity of the as-deposited Si/ f^{latrural} Fe₇₅Zr₂₅ (25 1nm) 57 Fe₇₅Zr₂₅ (12 1nm) $_{\text{lo}}$ multilayer at di erent applied stresses. The intensity shown on y-axis has been multiplied by a factor of 100, for clarity.

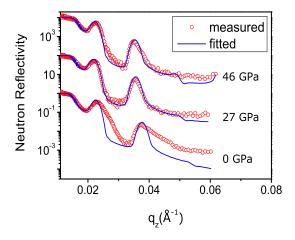


FIG. 3: (color on line) N eutron re-ectivity of the as-deposited Si/ $_{1}^{\text{natural}}$ Fe₇₅Zr₂₅ (25 1 nm) $_{2}^{\text{natural}}$ Fe₇₅Zr₂₅ (12 1 nm) $_{10}^{\text{n}}$ multilayer prepared with applied stresses of 0, 27 and 46 GPa. The intensity shown on y-axis has been multiplied by a factor of 100, for clarity.

peaks m ay arise due to incorporation of some free volume which m ay result in some internal strain or stresses during the growth of the lim and might cause an asymmetry in the scattering length density. For the samples which were prepared in the bent state, the release of bending results into an applied external stress on to the multilayer which eventually results in annihilation of free volume. A more detailed discussion related to this issue is given in the next sections.

The neutron re ectivity pattern was tted using a computer program based on Parratt's form alism 25 and it was found that the pattern could not be tted assuming sharp interfaces; instead a thin inter-layer of thickness (1 0.5) nm with the mean scattering length density of the two layers had to be introduced as inter-diused layer. This means that already at room temperature

there is som e am ount of interdi usion in the multilayer. The tted parameters gives the structure of the multilayers: Si/ $f^{\text{natrural}}Fe_{75}Zr_{25}$ (25 1 nm) $f^{\text{natrural}}Fe_{75}Zr_{25}$ (12 1 nm) $f^{\text{natrural}}Fe_{75}Zr_{25}$ (12 1 nm) $f^{\text{natrural}}Fe_{75}Zr_{25}$ (12 1 nm)

B. Crystallization Behavior

Prior to di usion measurements thermal stability of the samples was studied with grazing incidence x-ray di raction. All the samples were annealed together in a vacuum fumace in the tem perature range of 373-573 K with 100 K step. In the as-prepared state all the sam ples show a di use maxim a cantered around 2 = 44.6, with a width of about 4-5 (see Fig. 4), which means that the sam ples are x-ray am orphous in the as-prepared state. The width of the diuse maxima is comparable to the iron based am orphous alloys. The average interatom ic distance can be estimated using the relation, 26 $a = 1.23 = 2 \sin , where$ is taken to be the angle at the center of the di use maxima, and the factor 123 is a geom etric factor which rationalizes the nearest neighbor distance with the spacing between 'pseudo-close packed planes'. As shown in the g. 4, with an increase in the applied stress the position of the am orphous maxim a shifts towards higher angle side indicating a decrease in the average inter-atom ic distance as shown in the inset of the gure. Such a decrease in the average interatom ic distance may be caused due to applied compressive stress. A fter annealing at 373 K, the broad hum p becom es narrow (width 1) and a nano-com posite structure is found, as shown in q.5. The peak shape from the nano-com posite structure could be tted only by deconvoluting it into two lines, one corresponding to the parent am orphous phase and the second to a nanocrystalline bcc-Fe phase. The area ratio of am orphous phase as determined from the tting of XRD data was in the range of 15-25%. A slight decrease in the area ratio of the am orphous phase was observed. On further annealing at 473 and 573 K, no signi cant changes in the XRD pattern of the samples were observed as shown in q.5. After annealing at di erent tem peratures the position of Bragg peak shifts towards higher angle indicating a further decrease in the interatom ic spacing. Such a decrease in interatom ic spacing is related with structural relaxation and is a consequence of annihilation of free volume. The grain size of the nanocrystals was about 10 nm, which increases marginally with an increase in the annealing tem perature as shown in q.6.

C rystallization behavior of the sam ples was also studied using conversion electron M ossbauer spectroscopy (CEMS). Sam ples prepared with and without applied stress were annealed at high temperatures. Fig. 7 compares CEMS pattern of a sam ple prepared with and without applied stress before and after annealing at 473 K. The CEMS patterns were tted assuming a sextate due to Fe nanocrystals and a doublet due to am orphous phase. Even in the as-deposited state a sextate with hyper ne

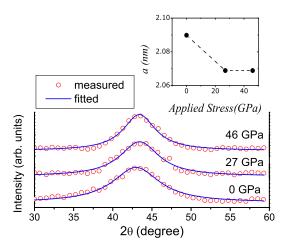


FIG. 4: (color online) X -ray di raction pattern of the isotopic multilayers in the as-deposited state. The measurements were carried out in the grazing incidence geometry using Cu-K x-rays. The inset in the gure shows the change in inter-atom ic distance as a function of annealing temperature.

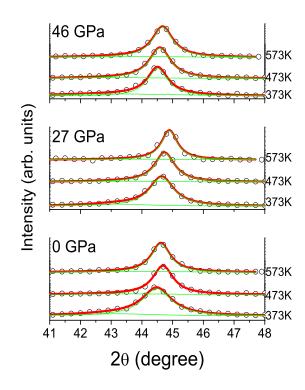


FIG. 5: (color online) G razing incidence x-ray di raction pattern of Si/ $f^{\text{latrural}} Fe_{75} Z\, r_{25}$ (25 $\,1\,$ nm)/ $^{57} Fe_{75} Z\, r_{25}$ (12 $\,1\,$ nm) l_{10} multilayer prepared with an applied stress of 0, 27 and 46 GPa after annealing at di erent tem peratures. Open circles represents the m easured data and the solid lines are t to them .

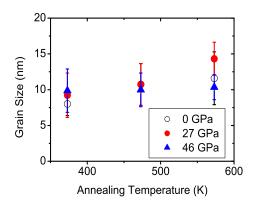


FIG. 6: (color online) A verage grain size as a function of annealing temperature shown representatively for a sample prepared with an applied stress of 0, 27 and 46 GPa.

eld of about 10 Tesla was found to be present. However, the area ratio of this sextate is very small. This indicates that there is a small amount of magnetic alloy while most of the alloy is not ferrom agnetic. As the sam ples were annealed the contribution of this magnetic phase increases indicating an enhancement in the volume fraction of nanocrystalline Fe in agreement with the XRD results. It may be noted that the hyper needlafter annealing remains in the range of 18-23 Tesla while that of pure Fe is 33.3 Tesla. The reduced magnetic moment could result due to some thermal uctuations. Table I compares the tted values for the dierent cases as shown in g.7.

TABLE I:Fitted CEMS param eters for the sample prepared with and without an applied stress in the as-deposited state and after annealing at $473~\rm K$.

Sam ple	Sam ple Condition	A verage Hyper ne Field (T)	A verage Q uadrupole (m m s 1)
0 G Pa 0 G pa 27 G Pa 27 G pa 46 G Pa 46 G pa	A s-deposited 473 K, 1 hour A s-deposited 473 K, 1 hour A s-deposited 473 K, 1 hour	10.8 0.5 T 18.4 1.3 T 10.2 0.9 T 23.4 0.8 T 13.0 0.2 T 22.5 1.5 T	0.40 0.01 0.43 0.01 0.44 0.01 0.70 0.01 0.44 0.01 0.42 0.01

MOKE measurements were also performed to understand the changes in the magnetic properties of the system during amorphous to nanocomposite phases. The sample prepared without an applied stress exhibited no anisotropy as a function of azimuthal angle in the coercivity. While the samples prepared with an applied stress clearly show uniaxial anisotropy, which persists even after the nanocrystallization of the lms (see g.8). This con ms that the bending stress induced in the lms persists even after nanocrystallization.

Form ation of a nano-composite phase after primary crystallization of the amorphous phase is a general phe-

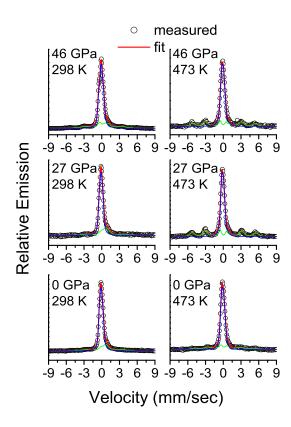
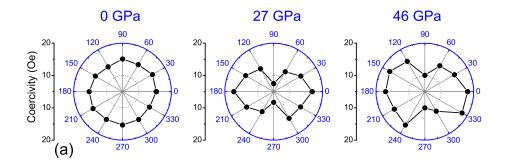


FIG. 7: (color online) Conversion electron Mossbauer spectroscopy (CEMS) pattern of Si/ $\rm f^{atru\,ra\,l}Fe_{75}\,Z\,r_{25}$ (25 $\,1\,$ nm)/ $\rm ^{57}\,Fe_{75}\,Z\,r_{25}$ (12 $\,1\,$ nm) $\rm l_{10}$ multilayer prepared with an applied stress of 0, 27 and 46 GPa in the as-deposited state and after annealing at 473 K .

nom enon in am orphous alloys. Offen, it was observed that am orphous binary alloys crystallize in two steps. The primary crystallization reaction of most of amorphous alloys leads to an evolution of nanocrystalline m icrostructures whereas the phase formed after the second stage results in an intermetallic compound along with the nanocrystalline phase. The nominal reaction for such crystallization process had been given as: am orphous! + am orphous! + ; where is the primary phase that precipitates out from the amorphous matrix and is an interm etallic com pound. 2,11,12 In the present case crystallization of the am orphous phase can be regarded as the primary crystallization process and as evident from the x-ray data, the am orphous phase co-exists along with grains of Fe. However, the primary crystallization tem perature for the present case was found to be very low as com pared with $\operatorname{Fe_{67}Zr_{33}}$ am orphous alloy. 21 Since in the present case for $Fe_{75}Zr_{25}$ alloy, the Zr content is slightly lower, a decrease in crystallization temperature is not very surprising. In order to further con m the structure of the alloy, a thin Im with even lower Zr content was deposited under identical conditions of sputtering. The composition of this lm was Fe₈₀ Zr₂₀. The XRD pattern



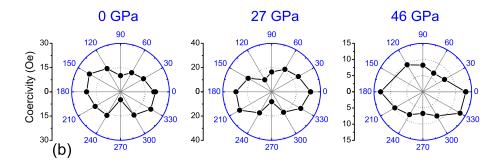


FIG. 8: (Color online) MOKE m easurements on Si/ $f^{\rm natrural}$ Fe₇₅Zr₂₅ (25 1 nm)/ 57 Fe₇₅Zr₂₅ (12 1 nm) $_{\rm h0}$ multilayer prepared with an applied stress of 0, 27 and 46 GPa in the as-deposited state (a) and after annealing at 473 K (b).

of this lm showed a narrow peak even in the as-prepared state (not shown in the gure), indicating that the structure forms a nanocrystalline state. Such a decrease in the primary crystallization temperature was also observed in an ion beam sputtered $Fe_{85}Zr_{15}$ sample, 28,29 and a phenomenon analogue to surface crystallization in amorphous alloy ribbons 30,31,32,33 was found responsible for early crystallization of amorphous $Fe_{85}Zr_{15}$ lm in the thin lm state.

For the am orphous thin Im formed by vapor deposition, the e ective quenching rate is very high which results in a higher quenched-in free volume and results in an early crystallization of the am orphous phase as observed in the present case. In order to further understand the crystallization behavior of the alloy, DSC measurements were carried out under a constant heating rate of 0.33 K/s. It was found that a very broad hump appears around 450 K and a relatively sharp peak appears around 613 K in all the three sam ples. The hum p appearing at 450 K can be estimated as rst crystallization step while relatively sharp peak corresponds to second crystallization step. From the XRD results, the rst crystallization event was observed as early as 373 K, where the samples were annealed for 1 hour, in the DSC scan since the sam ples were heated at a much faster rate, the crystalliza-

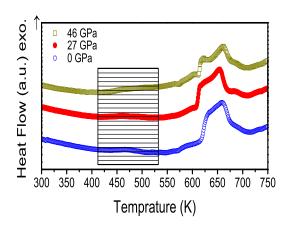


FIG.9: (color online) DCS scans of the Si/ $_{1}^{\text{natrural}}$ Fe₇₅Zr₂₅ (25 1 nm)/ $_{2}^{\text{57}}$ Fe₇₅Zr₂₅ (12 1 nm) $_{1}$ 0 m ultilayer prepared with an applied stress of 0, 27 and 46 GPa. The shaded region shown in the gure correspondences to the tem perature range used for di usion measurements.

tion event was observed at higher temperature as shown in g. 9. In a number of studies performed on bulk or thick Ims (thickness few m), it has been found that the heat release during the sts crystallization event is signi cantly smaller compared to the second crystallization event due to a slower di usion at lower tem perature. 34 In A Hoased glasses, Foley et al³⁵ have studied the crystallization behavior using transm ission electron m icroscopy (TEM) and DSC.W hile growth of nanocrystals was conrm ed by TEM, there was no evidence of primary crystallization with DSC. Smalldi usion of the constituents was argued for the observed behavior. In their case, they observed that, for di usivity, D $1 \ 10^{19} \ m^2 s^1$, the level of heat output is nearly undetectable in DSC measurements, which requires a signal on the order of 0.1 mW or greater. Unless the value of D was at least two orders of magnitude larger, the signal will be close to the noise level of the DSC. It may be noted that in the present case, the iron self-di usivity around 400 K, is of the order of 10²¹ m²s¹ (as shown in later sections). Further, the grain-size as determined with XRD results was about 10 nm, the heat release for the form ation of small grain sizes is expected to be small. In addition, the DSC measurements in the present case were performed in relatively thin lm (370 nm) and the total mass exposed during DSC measurements was only 65 gm which explains small heat release during the rst crystallization event, in spite of the high sensitivity of the sensor used during DSC measurements. The presence of peak around 613 K, can be understood as second crystallization step. The onset of second crystallization temperature was found around (608 5) K for all the 3 samples and there was no systematic e ect of applied stress on the second crystallization temperature.

C . Self-D i usion M easurem ents - T im e $\label{eq:D} D \ \mbox{ependence}$

With the observed them albehavior of the samples, for di usion m easurem ents, a tem perature range for diffusion annealing was chosen from 413-533 K in order to study di usion in the nano-com posite state. This tem perature region is also indicated in g. 8 as shaded area. The three sam ples prepared with an applied compressive stress of 0, 27 and 46 GPa were rst pre-annealed at 373 K for 0.5 hour to obtain the nano-com posite phase. For studying the time dependence of diusivity, the samples were further annealed at 473 K and neutron re ectivity m easurem ents were carried out after each annealing. In order to m in im ize the uctuations due to a possible variation in the tem perature, all the samples were annealed simultaneously in the furnace. Fig. 10 shows a plot of neutron re ectivities as a function of annealing time at 473 K.A relatively small time step was chosen in order to observe the structural relaxation of the samples. As can be seen from the qure, after annealing, the intensity at the Bragg peak decays. The initial decay was

found to be much faster as compared to that with later annealing time. The decay of the Bragg peak intensity can be used to calculate the di usion coe cient using the expression³⁶:

$$ln[I(t)=I(0)] = 8^2 n^2 D(T) t=d^2;$$
 (3)

where I (0) is the intensity before annealing and I (t) is the intensity after annealing time t at temperature T . The di usion length L $_{\rm d}$ is related to di usivity through the relation:

$$L_{d} = \stackrel{p}{=} \frac{}{2D (T)t;}$$
 (4)

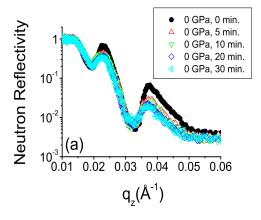
where t is the annealing time. The height of the B ragg peak was determined after subtracting the background due to Fresnel rejectivity by multiplying the data by a factor of \mathbf{q}^4 , where \mathbf{q} is the momentum transfer. Fig. 11 shows an evolution of the dijusion length as a function of annealing time at 473 K. As can be seen from the gure, the dijusion lengths below an annealing time of 600 s were found to increase much faster as compared to later annealing times. Such behavior in evolution of the dijusion length was also observed for Fe $_{67}$ Z r_{33} am orphous sample 21 and is a direct consequence of structural relaxation in the structures. 37,38

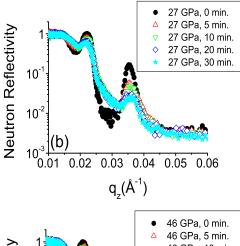
It is interesting to see that for the sample prepared without any stress, the di usion length increased much faster as compared to the samples prepared with an applied stress. As it is evident from the structural and magnetic measurements, samples prepared with an applied stress exhibited a more relaxed state as compared to that obtained without an applied stress. It is expected that structural relaxation would be more dominant for the sample prepared without an applied stress. The overall magnitude of the di usion length follows the strength of applied stress and the degree of relaxation is proportional.

D . Self-D i usion M easurem ents - Tem perature D ependence

In order to measure the activation energy for diusion, the sam ples were annealed in the temperature range of 413-533 K with a step of 40 K. As can be seen from the g.11, after an annealing time of 1800 s, in all cases, the fast relaxation process was almost completed, therefore for the calculation of the activation energy of the system all the samples were annealed for 1800 s at the above mentioned temperatures. It may be noted that annealing for 1800 s may not produce a fully relaxed state of the structure, even though for a comparison of diusivities for the samples prepared with dierent applied stress, the time for diusion annealing was kept constant.

Fig. 12 shows the neutron re ectivity pattern obtained after annealing at dierent temperatures. Again in order to minimize a possible uctuation in the temperature





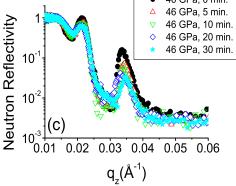


FIG. 10: (color online) D ecay of the B ragg peak intensity as a function of annealing time at $473 \, \text{K}$ for the sample prepared without an applied stress (a) with an applied stress of $27 \, \text{GPa}$ (b) and with an applied stress of $46 \, \text{GPa}$ (c).

and annealing conditions, all the three sam ples were annealed simultaneously in the furnace. For a comparison, the neutron rejectivity pattern in the as-prepared state is also shown in the gure. As evident from XRD and CEMS measurements, after annealing the samples undergo from the amorphous to the nano-composite state, the intensity at the Bragg peaks increases marginally in the neutron rejectivity patterns. In a previous study, it was observed that at the event of primary crystallization in the amorphous $Fe_{67}Zr_{33}$ alloy²¹ the neutron rejectivity pattern of an $[^{natural}Fe_{67}Zr_{33}]$ (9 nm) $[^{natural}Fe_{67}Zr_{33}]$ (9 nm) $[^{natural}Fe_{67}Zr_{33}]$ (9 nm)

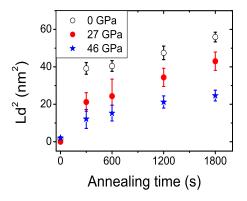
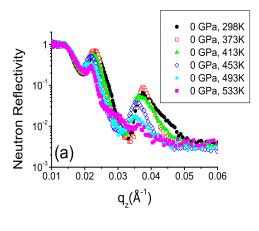
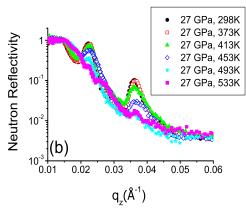


FIG. 11: (color online)Evolution of diusion length as a function of annealing time and applied stress at 473 K in nanocomposite Si/[1 atruralFe $_{75}$ Zr $_{25}$ (25 1 nm)/ 57 Fe $_{75}$ Zr $_{25}$ (12 1 nm) $_{10}$.

nm) 20 multilayer, showed an increase in the intensity at the Bragg peak by a factor as high as 10, as com pared to the as-deposited sample. Also the x-ray re ectivity pattern showed an appearance of a Bragg peak due to crystallization accompanied by a phase separation in the alloy. In the present case however, after annealing at 373 K, the am orphous phase nanocrystallize, but the intensity at the Bragg peak increases only marginally (<10%). Also as shown in the g.13, no Bragg peak or structure due to a chemical period appeared up to 573 K in the XRR pattern. This indicates that the primary crystallization behavior of $Fe_{75}Zr_{25}$ alloy is di erent as compared to that of previously studied $Fe_{67}Zr_{33}$ alloy.²¹ However, since the matrix obtained after nanocrystallization showed no further signi cant changes between the tem perature range 373-575 K (see also q. 8), it is expected that the di usion process would be not interfered by structural changes. As shown in g. 12, the intensity at both the Bragg peaks decreases with increase in annealing tem perature and after annealing at 533 K, the Braggpeak intensity almost vanishes. This indicates that after annealing at 533 K , both the natural and $^{57}\mbox{Fe}$ are layers almost completely diused. With the procedure discussed in the previous section, the di usivity at each tem perature was obtained. Fig. 14 shows a plot of diusivities obtained with both the Bragg peaks for the three sam ples. As can be seen from the gure, both the Bragg peaks yield sim ilar di usivities within the experimental errors. The error bars in the present case are basically representing the errors in determ ining the height of the Bragg peaks obtained from a peak tting procedure.

The values for the di usivity obtained for the three sam ples at the abovem entioned tem peratures (along w ith the separately annealed sam ples at 473 K), could be tted to the relation, $lnD=lnD_0\ (E=k_B\,T)$, where D_0 , E and T are the pre-exponential factor, the activation energy and the annealing tem perature respectively and k_B is the Boltzm ann constant. In all the three cases the logarithm of di usivity follows A rrhenius behavior and accordingly,





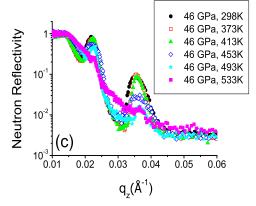


FIG. 12: (color online) Decay of the Bragg peak intensity as a function of annealing temperature for the sample prepared without an applied stress (a) with an applied stress of 27 GPa (b) and with an applied stress of 46 GPa (c).

the activation energy and the pre-exponential factor for iron self-di usion in Fe $_{75}$ Z r_{25} alloy was obtained. The observed values of both the E and D $_0$ are given in table II along with the values obtained for am orphous Fe $_{67}$ Z r_{33} alloy. Fig. 15 shows a plot of di usivities obtained from the 1st order B ragg peak for the sample at 0, 27 and 46 GPa. The activation energy was found to increase with an increase in the strength of applied compressive stress (a steeper slope was observed with an increase in the

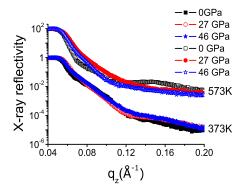


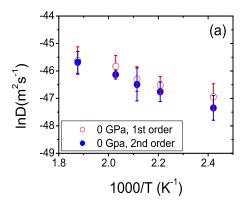
FIG. 13: (color online)X -ray re ectivity pattern of the Si/ $f^{\rm latrural}$ Fe₇₅Zr₂₅ (25 1 nm)/ 57 Fe₇₅Zr₂₅ (12 1 nm) $_{\rm lo}$ m ultilayers prepared w ith and w ithout applied stress after annealing at 373 and 473 K

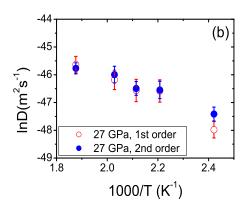
TABLE II: A ctivation energy and the pre-exponential factor for iron self-di usion in nanocrystalline $\mathrm{Si/}[^{\mathrm{natrural}}\mathrm{Fe_{15}}\,\mathrm{Z}\,\mathrm{r_{25}}$ (25 1 nm) $^{\mathrm{57}}\mathrm{Fe_{75}}\,\mathrm{Z}\,\mathrm{r_{25}}$ (12 1 nm) $^{\mathrm{10}}\mathrm{m}$ ultilayers as a function of applied stress during sample preparation. Both the activation energy and the pre-factor represent the statistical averaged values obtained from the 1st and 2nd order B ragg peaks.

Sam ple	Sam ple condition	A ctivation energy (E, eV)	P refactor (D ₀ , m ² s ¹)
nano.Fe ₇₅ Zr ₂₅ nano.Fe ₇₅ Zr ₂₅ nano.Fe ₇₅ Zr ₂₅ am orphousFe ₆₇ Zr ₃₃	0 G P a 27 G P a 46 G P a	0.24 0.05 0.31 0.05 0.51 0.05 0.38 0.05	3 10 ¹⁸ ¹ 1 10 ¹⁷ ¹ 1 10 ¹⁵ ¹ 3 10 ¹⁸ ¹

applied stress). The result gives a clear indication that di usivity for the sample prepared with applied stress is much slower as compared with that prepared without an applied stress. This result also supports the time dependence of the di usivity as shown in g.11.

In an earlier study K lugkist et al^{39,40} studied Co and Zr self-di usion in am orphous CoZralloy using Radioactive tracerm ethod as a function of pressure and tem perature dependence. It was found that the pressure dependence for Coself-diusion is extremely small while for Zrselfdi usion it is of the order of one activation volume. On the basis of obtained results it was concluded that Zrdiffuses via therm aldefects, whereas vacancy like therm al defects can be ruled out for Co self-di usion. However, our results clearly indicates a decrease in di usivity with an increase in applied stress. Here we would like to point out that a direct comparison between the studies perform ed earlier 39,40 with that of our results could not be m ade. The following points are important to understand our results (i) The neutron re ectom etry technique o ers a depth resolution in sub nanom eter range it is possible to measure initial stage of self-di usion in a alloy unlike





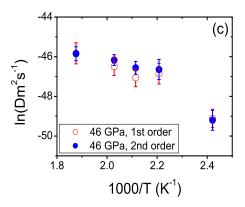


FIG. 14: (color online) A rhenius behavior of the di usivity obtained from the 1st and 2nd order Bragg peaks for sam ples prepared with an applied stress of 0 GPa (a), 27 GPa (b) and 46 GPa (c).

conventional techniques e.g. SIM S or radioactive tracer method (ii) As mentioned already that in our case, the alloy could have not attained a fully relaxes state as preannealing time was very short compared with that in literature. Combining the above mentioned points, it is not surprising that there is a strong dependence of self-diusion of Fe on applied stress, which points out that in the initial state the diusion mechanism could be dierent.

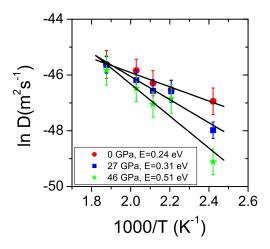


FIG.15: (color online) A ctivation energy and pre-exponential factor for di usion as a function of applied stress in $\mathrm{Si/}\,f^{\mathrm{1a\,tru\,ra\,l}}\mathrm{Fe_{75}\,Z\,r_{25}}$ (25 $\,1\,\mathrm{nm}\,)/^{57}\,\mathrm{Fe_{75}\,Z\,r_{25}}$ (12 $\,1\,\mathrm{nm}\,)_{\,10}^{\,}\,\mathrm{m\,ultilayer}.$ The data corresponds to the di usivity obtained from the 1st order B ragg peak. The sample prepared with the highest applied gives and activation energy more than twice as compared with the sample prepared without an applied stress. The detailed values of activation energy and the pre-exponential factors are given in table II.

Com paring the di usivity for the sam ple prepared at 0 GPa with that of am orphous Fe₆₇ Zr₃₃ sample (also prepared at 0 GPa), the di usivity in the nano-composite state is slightly higher as compared to the amorphous sample. The activation energy for the nanocomposite sam ple was lower by 0.14 eV, while the pre-exponential factors were found to be exactly similar (see table II). An enhancement in diusivity in the nano-composite state is not unexpected due to presence of grains and grain-boundaries (GB), while the amorphous phase is expected to be free from grains and GBs. However the enhancement in diusivity in the present case is not as spectacular as observed e.g. in the FINEMET type nanocrystalline-Fe_{73:5}Si_{43:5}B₉Nb₃Cu₁ in which the Fe self-di usion showed a large enhancement over that in the parent am orphous phase. 41,42 It may be noted that in the present case the composition of the nanocom posite $Fe_{75}Zr_{25}$ alloy is also not sim ilar to the am orphous Fe₆₇Zr₃₃ alloy, therefore an enhancem ent in di usivity may also occur due to increased concentration of Fe. In another study self-di usion of iron was measured in the parent am orphous and nano-com posite Fe₈₅Zr₁₅ alloy thin Im produced by ion-beam sputtering. It was found that iron self-diusion in both amorphous and nano-com posite state was similar and found to occur exclusively through the GB regions which were am orphous in nature. 28 In the present case as well the GBs in the nano-com posite state are am orphous, which m ight happen due to the fact that in the nano-com posite state, the structure consists of a m ixture of nanocrystalline grains of Fe and remaining am orphous phase. The nanocrystalline grains of Fe would be surrounded by am orphous GBs and in such a situation a percolating path between the nanocrystals may not establish and diusivity in the nano-composite phase would be similar to that in the am orphous state.

On the other hand, the activation energy obtained for the sample prepared with highest applied stress was found to be larger (slower di usivity) as compared to the am orphous Fe₆₇Zr₃₃ sam ple. This is som ew hat surprising as the sample prepared even at the highest stress is also in the nano-composite state. In case the di usion mechanism is dominated by grains and GBs the e ective applied stress should result in an enhancement of the di usivity.43 As discussed earlier, an applied compressive stress produced a more relaxed state of the sample as compared to samples prepared without stress. If the di usion mechanism is dominated by a somewhat collective type m igration of atom s both in am orphous and nano-com posite case, annihilation of free volum e would result into a di usion mechanism involving a small group of atom s.

IV. CONCLUSIONS

In the present work, the e ect of com pressive stress on self-di usion of iron in chem ically hom ogenous multilay-

ers of FeZr/⁵⁷FeZr was investigated. It was found that sam ples in the as-prepared state were am orphous and undergo primary crystallization when annealed at 373 K. The di usion measurements were performed in the nano-composite state and it was observed that with an increase in the strength of applied stress, the di usivity decreases as compared to the sam ple prepared without an applied stress. An applied compressive stress on to the multilayer produced a more relaxed state of the sample as seen from XRD. A di usion mechanism involving a small group of atom sexplains the observed di usivity in the chemically homogeneous multilayers.

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E lectronic address: m gupta@csr.emet.in

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